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(54) **METAL-INSULATOR-METAL STRUCTURE AND METHODS OF FABRICATION THEREOF**

(71) Applicant: **Taiwan Semiconductor Manufacturing Co., Ltd.**, Hsin-Chu (TW)

(72) Inventors: **Chih-Fan Huang**, Kaohsiung City (TW); **Hung-Chao Kao**, Taipei City (TW); **Yuan-Yang Hsiao**, Taipei (TW); **Tsung-Chieh Hsiao**, Changhua County (TW); **Hsiang-Ku Shen**, Hsinchu City (TW); **Hui-Chi Chen**, Hsinchu County (TW); **Dian-Hau Chen**, Hsinchu (TW); **Yen-Ming Chen**, Hsin-Chu County (TW)

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(57) **ABSTRACT**

The present disclosure is directed to a semiconductor device. The semiconductor device includes a multi-layer interconnect structure disposed over a substrate, a dielectric layer disposed over the multi-layer interconnect structure, and a metal-insulator-metal (MIM) capacitor disposed over the dielectric layer. The MIM capacitor includes a bottom electrode disposed on a top surface of the dielectric layer, a top electrode disposed above the bottom electrode, and an insulating layer interposed between the bottom electrode and the top electrode. The bottom electrode has a slanted sidewall with respect to the top surface of the dielectric layer. The top electrode has a vertical sidewall with respect to the top surface of the dielectric layer. The insulating layer covers the slanted sidewall of the bottom electrode.